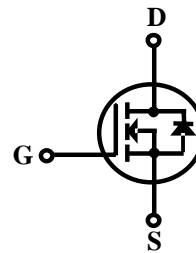


Features

- **N-Channel MOSFET**
- **BV_{DSS} (Minimum) : 200 V**
- **$R_{DS(ON)}$ (Maximum) : 0.4 ohm**
- **I_D : 9.0 A**
- **Q_g (Typical) : 26 nc**
- **P_D (@TC=25 °C) : 72 W**

General Description

This power MOSFET is produced in CHMC with advanced VDMOS technology of SAMWIN. This technology enable power MOSFET to have better characteristics, such as fast switching time, low on resistance, low gate charge and especially excellent avalanche characteristics. This power MOSFET is usually used at high efficient DC to DC converter block and SMPS. It's typical application is TV and monitor.



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{DSS}	Drain to Source Voltage	200	V
I_D	Continuous Drain Current (@Tc=25°C)	9	A
	Continuous Drain Current (@Tc=100°C)	6.8	A
I_{DM}	Drain Current Pulsed (Note 1)	36	A
V_{GS}	Gate to Source Voltage	±30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	160	mJ
E_{AR}	Repetitive Avalanche Energy (Note 1)	7.2	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.0	V/ns
P_D	Total Power Dissipation (@Tc=25°C)	72	W
	Derating Factor above 25°C	0.57	W/°C
T_{STG}, T_J	Operating junction temperature & Storage temperature	-55~+150	°C
T_L	Maximum Lead Temperature for soldering purpose, 1/8 from Case for 5 seconds.	300	°C

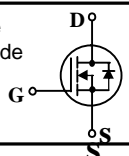
Thermal Characteristics

Symbol	Parameter	Value			Units
		Min	Typ	Max	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	-	-	1.73	°C/ W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	-	0.5	-	°C/ W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	-	-	62.5	°C/ W

Electrical Characteristics (Tc=25℃ unless otherwise noted)

Symbol	Parameter	Test Conditions	Value			Unit s
			Min	Typ	Max	
Off Characteristics						
BV _{DSS}	Drain- Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	200	-	-	V
ΔBV _{DSS} /ΔTj	Breakdown Voltage Temperature coefficient	I _D =250uA, referenced to 25℃	-	0.17	-	V/℃
I _{DSS}	Drain-Source Leakage Current	V _{DS} =200V, V _{GS} =0V	-	-	1	uA
		V _{DS} =160V, Tc=125℃				
I _{GSS}	Gate-Source Leakage Current	V _{GS} =30V, V _{DS} =0V	-	-	100	nA
	Gate-Source Leakage Reverse	V _{GS} =-30V, V _{DS} =0V	-	-	-100	nA
On Characteristics						
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2.0	-	4.0	V
R _{DS(ON)}	Static Drain-Source On-state Resistance	V _{GS} =10V, I _D =4.5A	-	-	0.4	ohm
Dynamic Characteristics						
Ciss	Input Capacitance	V _{GS} =0V, V _{DS} =25V f=1MHz	-	-	770	pF
Coss	Output Capacitance		-	-	120	
Crss	Reverse Transfer Capacitance		-	-	35	
Dynamic Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =100V, I _D =9A R _G =50ohm (Note4,5)	-	-	40	ns
t _r	Rise Time		-	-	140	
t _{d(off)}	Turn-off Delay Time		-	-	150	
t _f	Fall Time		-	-	140	
Q _g	Total Gate Charge	V _{DS} =160V, V _{GS} =10V, I _D =9A (Note4,5)	-	-	34	nC
Q _{gs}	Gate-Source Charge		-	4	-	
Q _{gd}	Gate-Drain Charge(Miller Charge)		-	10	-	

Source-Drain Diode Ratings and Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit.
I_S	Continuous Source Current	Integral Reverse p-n Junction Diode in the MOSFET 	-	-	9	A
I_{SM}	Pulsed Source Current		-	-	36	
V_{SD}	Diode Forward Voltage	$I_S=9A, V_{GS}=0V$	-	-	1.5	V
t_{rr}	Reverse Recovery Time	$I_S=9A, V_{GS}=0V$, $di_F/dt=100A/\mu s$	-	140	-	ns
Q_{rr}	Reverse Recovery Charge		-	0.77	-	uc

※NOTES

1. Repeativity rating: pulse width limited by junction temperature
2. $L=6.3mH, I_{AS}=9A, V_{DD}=50V, R_G=0ohm$, Starting $T_J=25^\circ C$
3. $I_{SD} \leq 9A, di/dt \leq 100A/\mu s, V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ C$
4. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
5. Essentially independent of operating temperature.

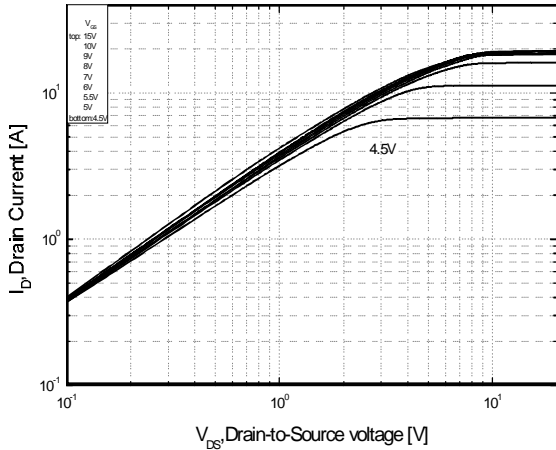


Fig 1. On-State Characteristics

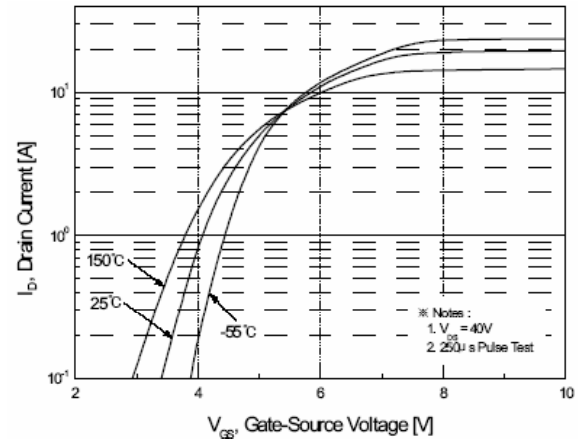


Fig 2. Transfer Characteristics

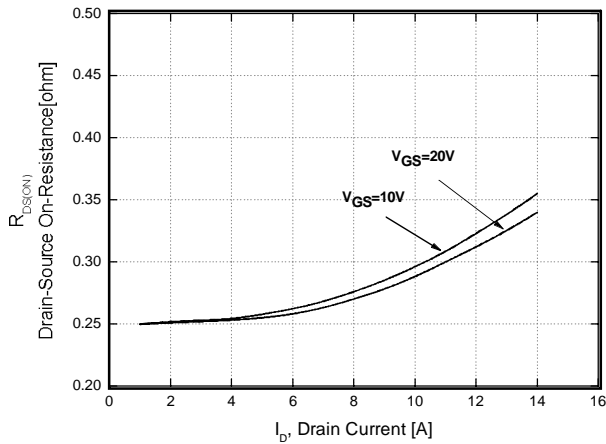


Fig 3. On Resistance Variation vs. Drain Current and Gate Voltage

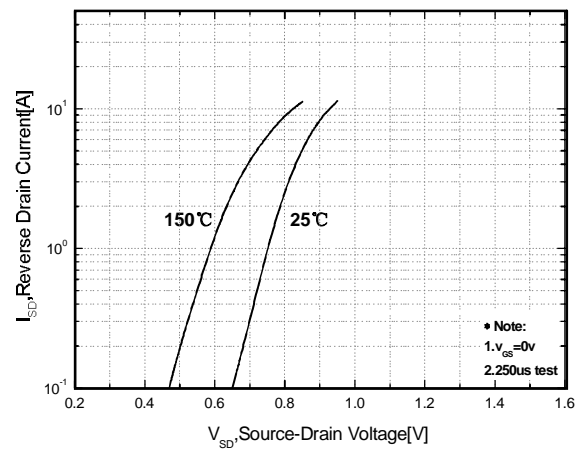


Fig 4. On State Current vs. Allowable Case Temperature

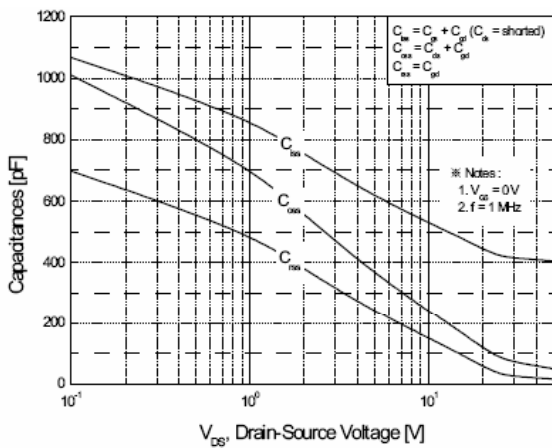


Fig 5. Capacitance Characteristics (Non-Repetitive)

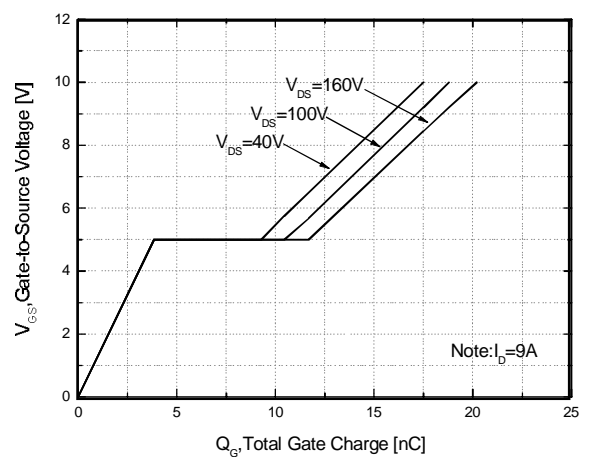
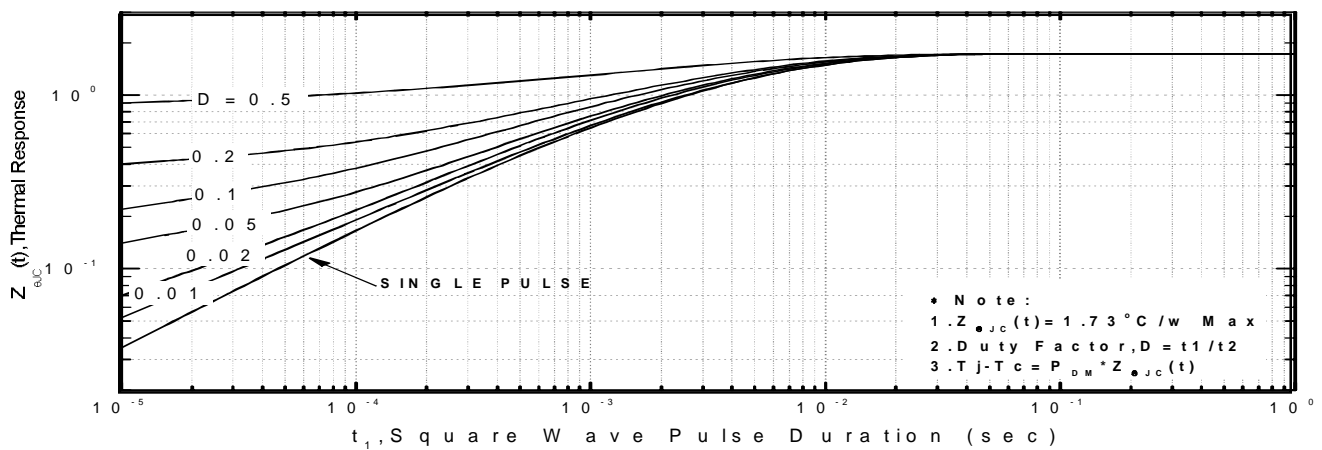
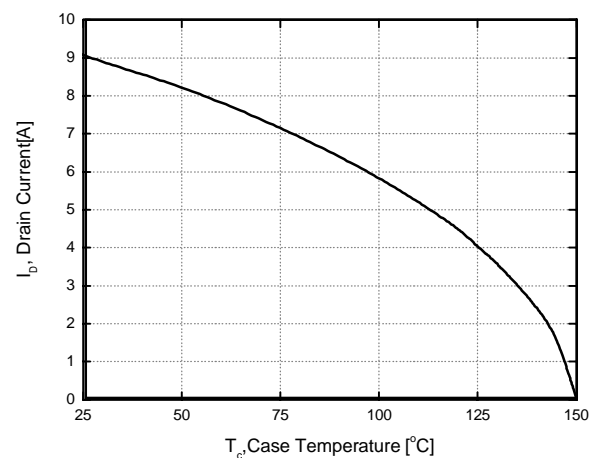
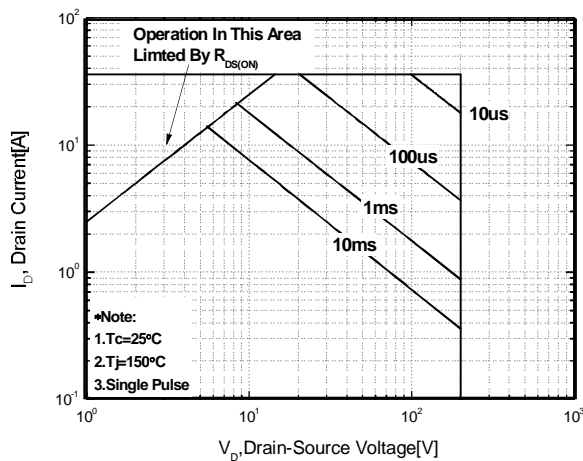
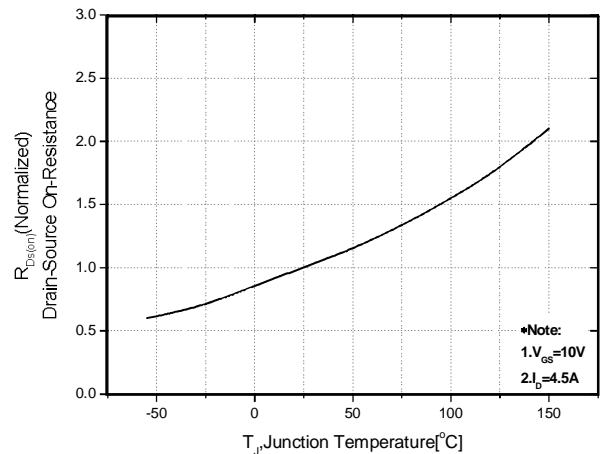
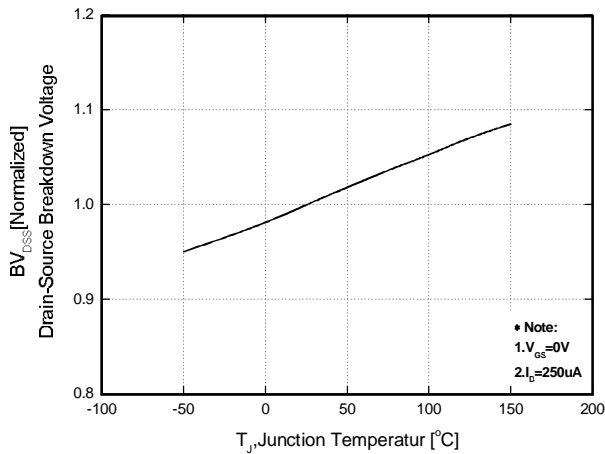


Fig 6. Gate Charge Characteristics



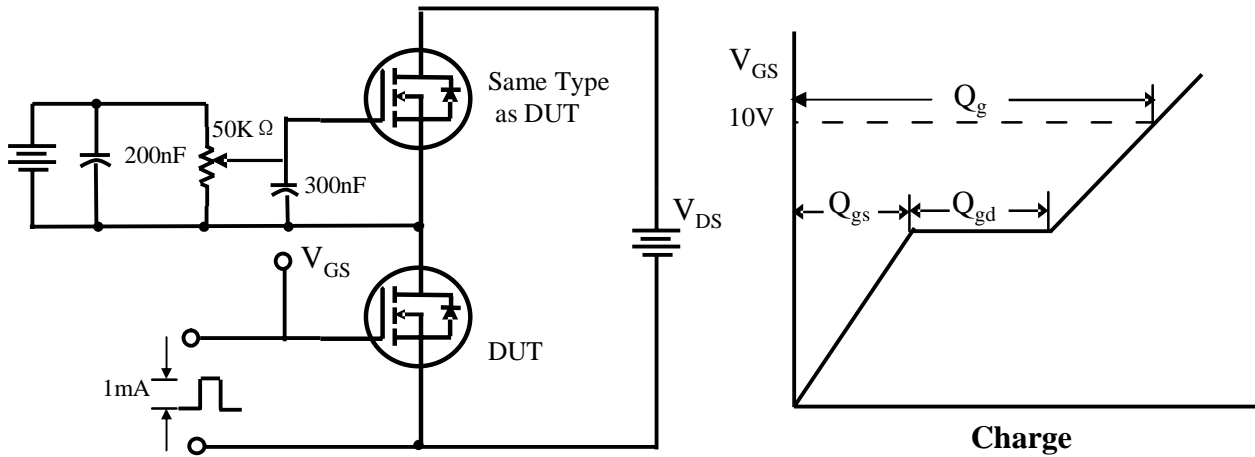


Fig 12. Gate Charge test Circuit & Waveforms

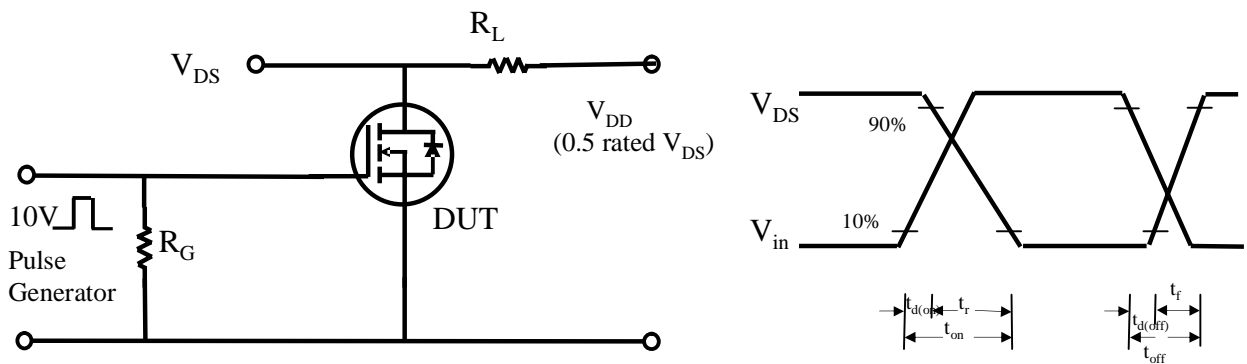


Fig 13. Switching test Circuit & Waveforms

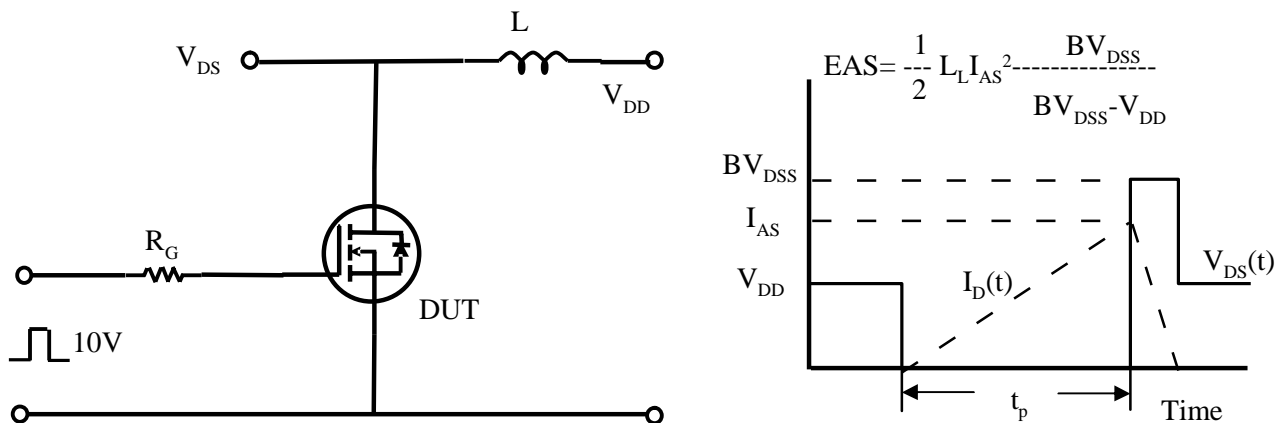


Fig 14. Unclamped Inductive Switching test Circuit & Waveforms

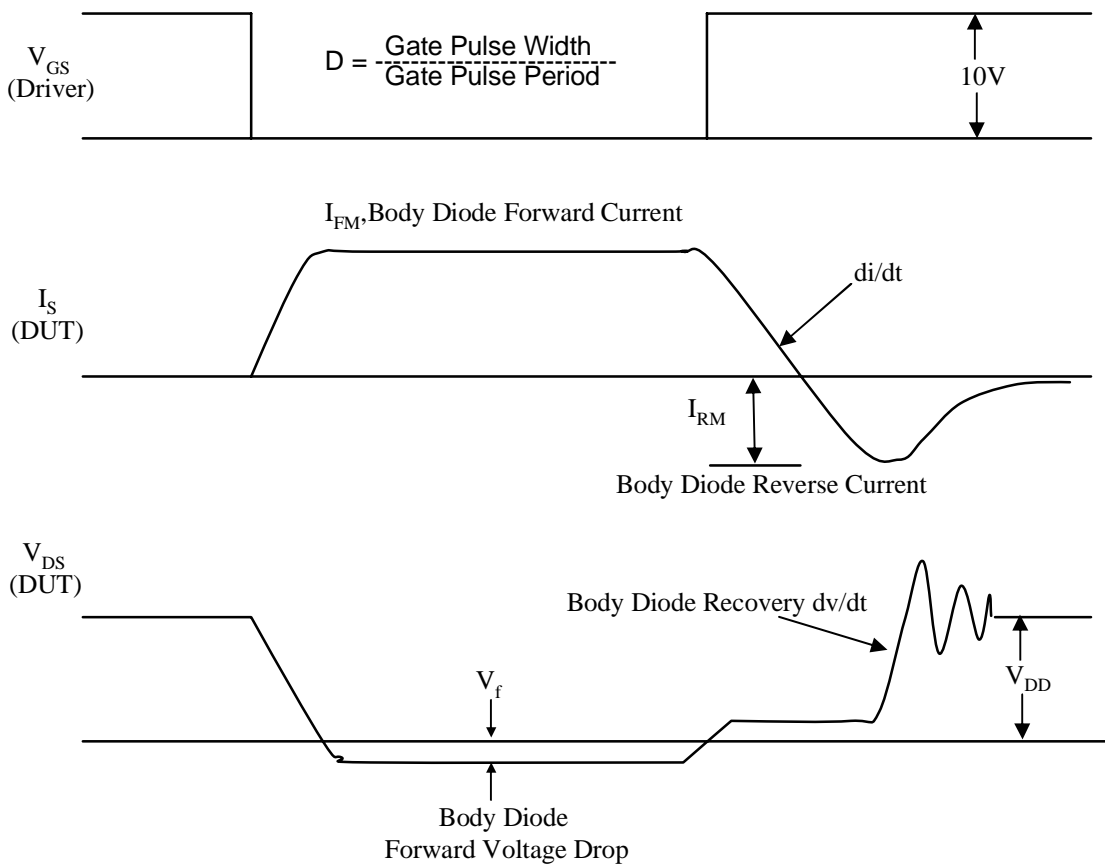
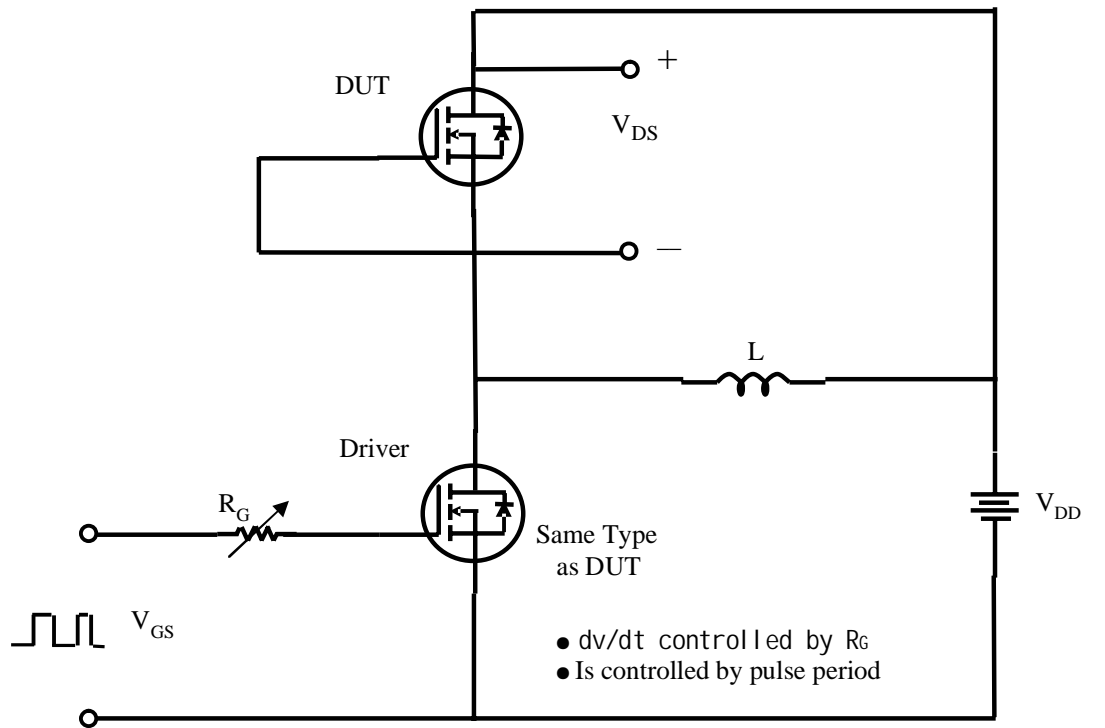


Fig 15. Peak Diode Recovery dv/dt test Circuit & Waveforms